

**1N4448**

**1N4448 SIGNAL DIODE**

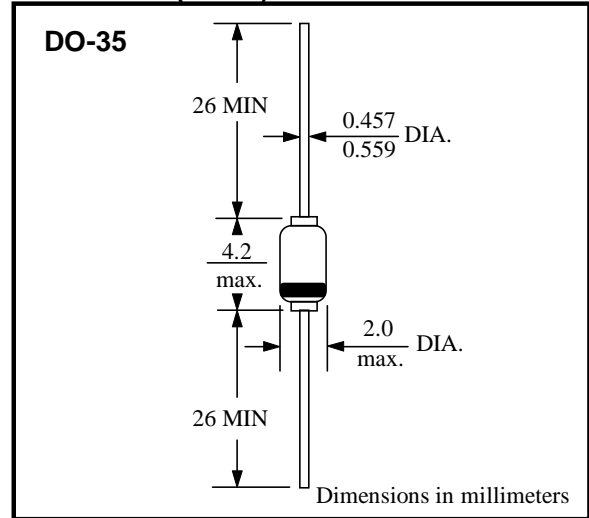
**Absolute Maximum Ratings (Ta=25°C)**

| Items                                 | Symbol | Ratings    | Unit |
|---------------------------------------|--------|------------|------|
| Reverse Voltage                       | VR     | 75         | V    |
| Reverse Recovery Time                 | trr    | 4          | ns   |
| Power Dissipation<br>3.33mW/°C (25°C) | P      | 500        | mW   |
| Forward Current                       | IF     | 500        | mA   |
| Junction Temp.                        | Tj     | -65 to 175 | °C   |
| Storage Temp.                         | Tstg   | -65 to 175 | °C   |

**Mechanical Data**

| Items       | Materials                  |
|-------------|----------------------------|
| Package     | DO-35                      |
| Case        | Hermetically sealed glass  |
| Lead/Finish | Double stud/Solder Plating |
| Chip        | Glass Passivated           |

**Dimensions (DO-35)**



**Electrical Characteristics (Ta=25°C)**

| Ratings   | Symbol  | Ratings            | Unit |
|---|---------|--------------------|------|
| Minimum Breakdown Voltage<br>IR= 5.0uA<br>IR= 100uA                   | BV      | 75<br>100          | V    |
| Peak Forward Surge Current PW= 1sec.                                  | IFsurge | 1.0                | A    |
| Maximum Forward Voltage<br>IF= 100mA                                  | VF      | 1.0                | V    |
| Maximum Reverse Current<br>VR= 20V<br>VR= 75V<br>VR= 20V, Tj= 150°C   | IR      | 0.025<br>5.0<br>50 | uA   |
| Maximum Junction Capacitance<br>VR= 0, f= 1 MHz                       | Cj      | 4                  | pF   |
| Maximum Reverse Recovery Time<br>IF= 10mA, VR= 6V, IRR= 1mA, RL= 100Ω | trr     | 4                  | ns   |